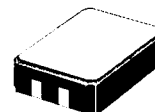




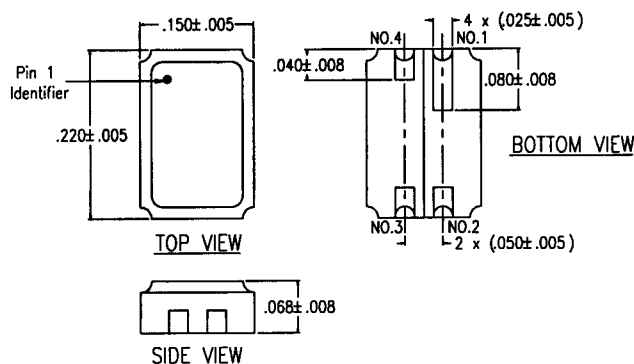
PRELIMINARY

SOLID STATE DEVICES, INC14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**Designer's Data Sheet****FEATURES:**

- Low Profile Surface Mount Package
- 200°C Operating, Eutectic Die Attach
- BVCEr and BVCEB to 600V
- Low Leakage at High Temperature
- High Gain, Low Saturation
- Available Screening, TX, TXV, or Space Level
- Designed for complimentary use with SFT5015

SFT5094**1 Amp
600 Volts
PNP TRANSISTOR****4 PIN CLCC****MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage (RBE=1K Ω)	V _{CEO} V _{CER}	400 600	Volts
Collector-Base Voltage	V _{CBO}	600	Volts
Emitter-Base Voltage	V _{EBO}	6	Volts
Collector Current	I _C	1	Amp
Base Current	I _B	0.5	Amps
Total Device Dissipation @ TC= 25°C @ TA= 25°C Derate above @ TC= 25°C	P _D P _D	1.0 0.4 5.7	Watts Watts mW/°C
Operating and Storage Temperature	T _j , T _{stg}	-65 to +200	°C
Thermal Resistance, Junction to Case Junction to Ambient	R _{θJC} R _{θJA}	175 440	°C/W

PACKAGE OUTLINE: 4 PIN CLCCPIN 1: COLLECTOR
PIN 2: EMITTER
PIN 3: BASE
PIN 4: N/C**NOTE:** All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.**DATA SHEET #: XP0015 A**

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ELECTRICAL CHARACTERISTICS (Per Transistor) @ $T_A=25^{\circ}\text{C}$ (Unless Otherwise Specified)

RATING		SYMBOL	MIN	MAX	UNIT
Collector-Emitter Breakdown Voltage (IC=1mA)* (IC=200μA, RBE=1KΩ)		BVCEO BVCER	400 600	---	Volts Volts
Collector- Base Breakdown Voltage (IC= 200μA)		BVCBO	600	---	Volts
Emitter-Base Breakdown Voltage (IE = 50μAdc)		BVEBO	6	---	Vdc
Collector Cutoff Current (VCB= 500Vdc) (VCB= 500 Vdc, TA=100°C)		ICBO	---	1.0 50	uAdc
Emitter Cutoff Current (VEB = 6 Vdc)		IEBO	---	1.0	uAdc
DC Current Gain * (IC= 1 mAdc, VCE= 10 Vdc) (IC= 25 mAdc, VCE= 10 Vdc) (IC=100 mAdc, VCE= 10 Vdc)		HFE	20 40 20	250 300 250	
Collector -Emitter Saturation Voltage * (IC= 25 mAdc, IB = 2.5 mAdc)		VCE(SAT)	---	500	mVdc
Base-Emitter Saturation Voltage 'IC= 25 mAdc, IB = 2.5 mAdc)		VBE(SAT)	---	1.0	Vdc
Current Gain Bandwidth Product * (IC= 10 mAdc, VCE= 10 Vdc, f= 10 MHz)		fT	25	---	MHz
Output Capacitance (VCB= 20 Vdc, IE= 0 Adc, f = 1.0 MHz)		Cob	---	10	pF
Delay Time	(VCC= 100V IC= 100 mA IB, IB2 = 10 mA)	td	---	500	ns
Rise Time		tr	---	1200	ns
Storage time		ts	---	2000	ns
Fall Time		tf	---	500	ns

 * Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2%

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.